

Datasheet

FS8205

Dual N-Channel Enhancement Mode Power MOSFET

For Reference Only

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FSC's
 Properties
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1. Features

1.1 Low on-resistance

1.1.1 $R_{DS(ON)} = 25 \text{ m}\Omega$ MAX. ($V_{GS} = 4.5\text{V}$, $I_D = 4\text{A}$)

1.1.2 $R_{DS(ON)} = 35 \text{ m}\Omega$ MAX. ($V_{GS} = 2.5\text{V}$, $I_D = 3\text{A}$)

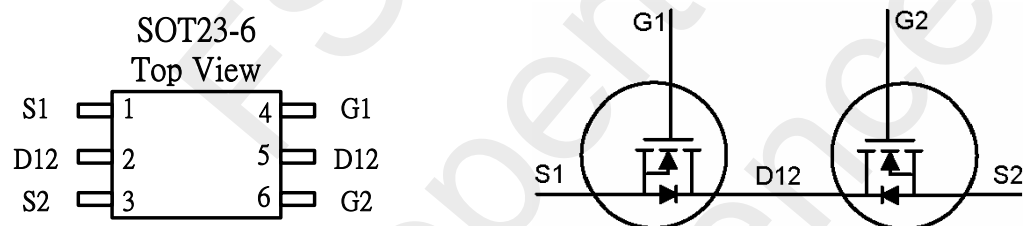
2. Applications

- Li-ion battery management applications

3. Ordering Information

Product Number	Description	Package Type	Quantity/Reel
FS8205	SOT23-6 package version	SOT23-6	3,000

4. Pin Assignment



5. Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	20	V
VGS	Gate-Source Voltage	±12	V
ID @TA = 25°C	Continuous Drain Current3	6	A
ID @TA = 70°C	Continuous Drain Current3	5	A
IDM	Pulsed Drain Current1	25	A
PD @TA = 25°C	Total Power Dissipation	1	W
	Linear Derating Factor	0.008	W/°C
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

6. Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient3	Max. 125	°C/W

7. Electrical Characteristics

Electrical Characteristics @ $T_j = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	20	-	-	V
$\Delta BV_{DSS} / \Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D = 1mA$	-	0.1	-	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS} = 4.5V, I_D = 4A$	-	21	25	m Ω
		$V_{GS} = 2.5V, I_D = 3A$	-	27	35	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	-	1.0	V
I_{DSS}	Drain-Source Leakage Current ($T_j = 25^\circ\text{C}$)	$V_{DS} = 20V, V_{GS} = 0V$	-	-	1	μA
	Drain-Source Leakage Current ($T_j = 70^\circ\text{C}$)	$V_{DS} = 20V, V_{GS} = 0V$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{GS} = \pm 10V$	-	-	± 10	μA

8. Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_S	Continuous Source Current (Body Diode)	$V_D = V_G = 0V, V_S = 1.2V$	-	-	0.83	A
V_{SD}	Forward On Voltage ²	$T_j = 25^\circ\text{C}, I_S = 1.25A, V_{GS} = 0V$	-	-	1.2	V

Notes :

1. Pulse width limited by Max. junction temperature.
2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Surface mounted on 1 in² copper pad of FR4 board : $208^\circ\text{C}/W$ when mounted on Min. copper pad.

9. Typical Characteristics

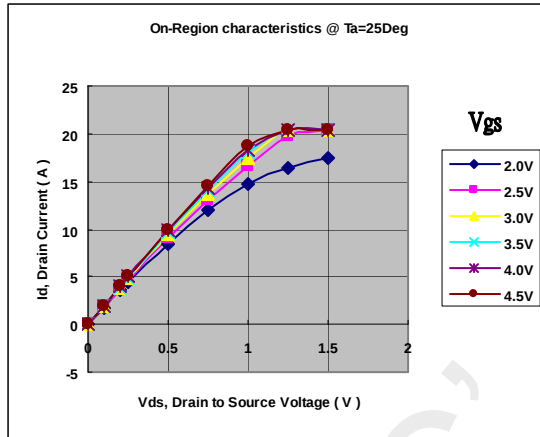


Fig 1. Typical Output Characteristics

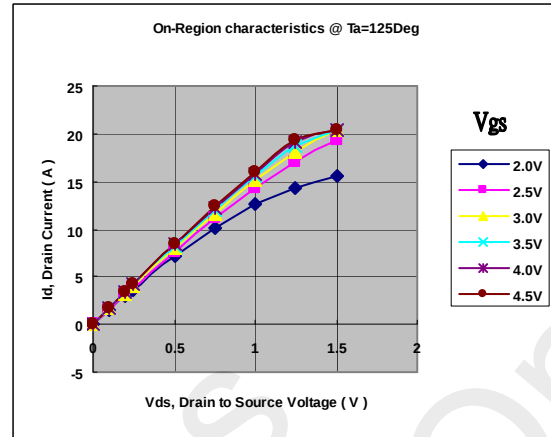


Fig 2. Typical Output Characteristics

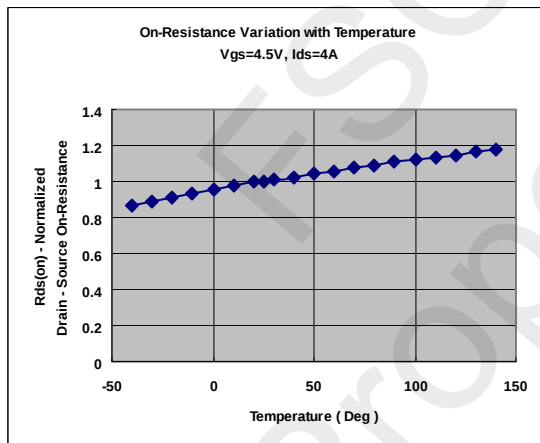


Fig 3. Normalized On-Resistance

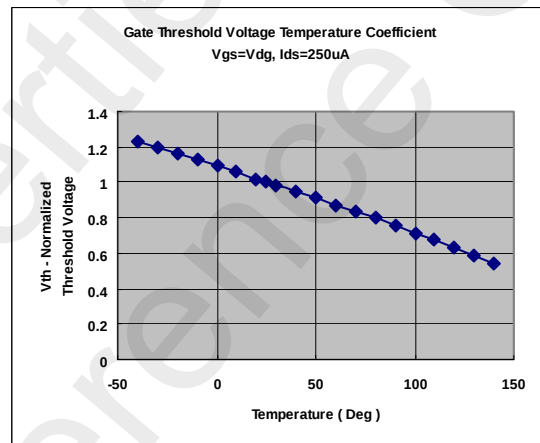


Fig 4. Gate Threshold Variation with Temperature

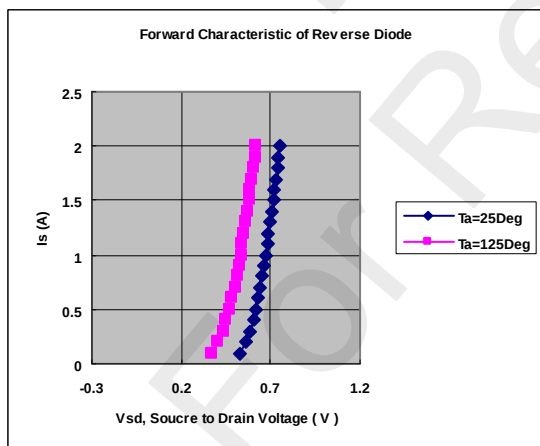
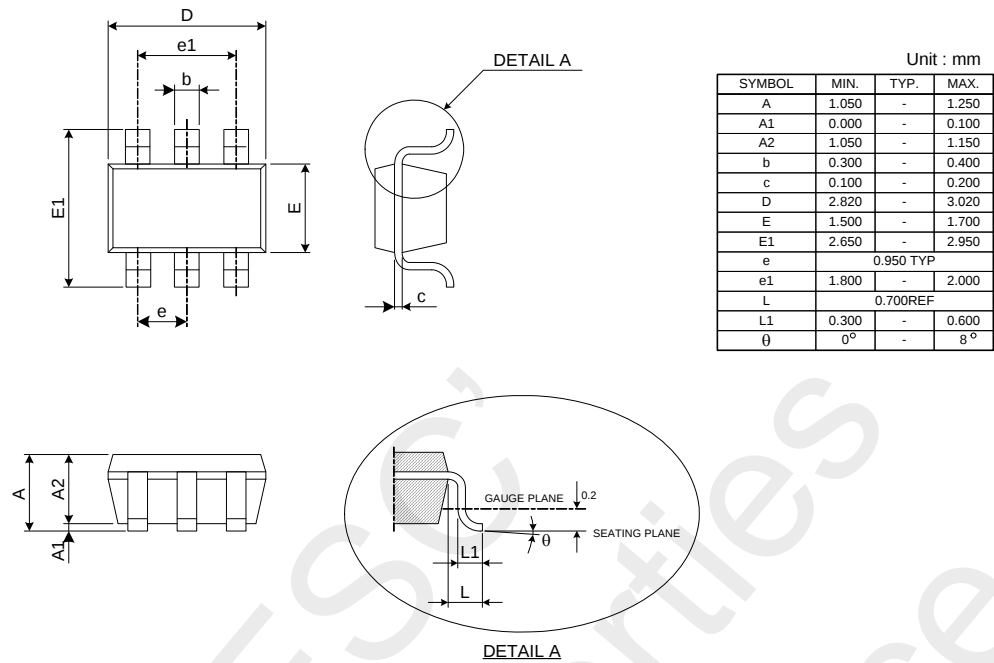


Fig 5. Forward Characteristic of Reverse Diode

10. Package Information



11. Revision History

Version	Date	Page	Description
1.0	2009/08/17	-	Version 1.0 released